

REMARKS

We are in receipt of the Office Action dated July 18, 2003 and the above amendment and following remarks are made in light thereof.

Claims 1, 5-13, 15-48 and 50-59 are pending in the application. Claims 5-13, 16, 17, 19, 20, 22, 23, 25 and 26 have been withdrawn from consideration pursuant to the election dated June 10, 1999, and are canceled herein. Claims 35-41 and 50-55 have been withdrawn pursuant to the election of species dated December 21, 2000.

Pursuant to the Office Action, Claims 1, 15, 18, 21, 24, 27-34 and 42-48 stand rejected for obviousness over Burr et al. 5,650,340. Claims 56-59 stand rejected for obviousness over Burr et al. '340 in view of Hook et al. 6,083,794, Mikoshiha JP 56060061 A and/or Okumura et al. 5,945,972. Claim 57 stands rejected for having an insufficient antecedent basis for the limitations "the first n-type impurity", the "second n-type impurity" and "the first and second p-type impurities." Claims 42-48 are objected to due to an informality in the claim language. Fig. 8 of the drawings is objected to failing to show the detail of the impurity distributions as shown in Fig. 3.

In response, claim 42 has been corrected in accordance with the examiner's request. A proposed substitute Fig. 8 accompanies this Amendment. Additionally, claim 57 has been amended to delete the references to the n-type and p-type impurities.

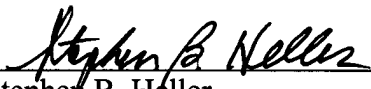
Turning to the substantive rejection of the pending claims, claims 1, 29, 42 and 56 have been amended to recite that the impurity region is formed at a depth in the range of 20 to 150 nm from the surface of the single crystal semiconductor substrate. This characteristic is already recited in claims 27, 34, 48 and 59, which are being canceled in this Amendment. Although the examiner contends that Burr et al. 6,093,951 teaches this characteristic at col. 8, lines 24-31, Burr et al. '951 merely teaches that the maximum

concentration of the pocket region should lie at least about 0.2 um below the top surface of the semiconductor substrate. This does not necessarily teach that the pocket region itself is located at a depth in the range of 20 to 150 nm from the stop of the substrate. Accordingly, applicant believes that claims 1, 15, 18, 21, 24, 27-34, 42-48 and 56-58 are not obvious in view of the cited art.

Based upon the foregoing, applicant believes that the application is now in condition for allowance and an early Office Action in this regard is earnestly solicited.

Respectfully submitted,

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